

N-Channel 150-V (D-S) MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
150	0.018 at $V_{GS} = 10$ V	75 ^d	64

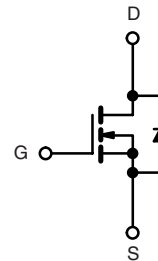
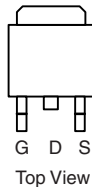
FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested


RoHS
COMPLIANT

APPLICATIONS

- Primary Side Switch
- Power Supplies

TO-263


N-Channel MOSFET

Ordering Information: SUM75N15-18P-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	75 ^d
		$T_C = 70$ °C	70
Pulsed Drain Current	I_{DM}	180	A
Avalanche Current	I_{AS}	50	
Single Avalanche Energy ^a	E_{AS}	125	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	312.5 ^b
		$T_A = 25$ °C ^c	3.12
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).
- Package limited.



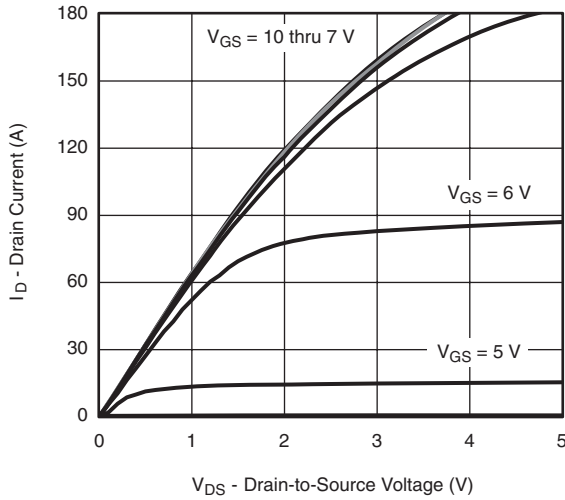
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		4.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0148	0.018	Ω
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.0296	0.036	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		55		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 75\text{ V}, f = 1\text{ MHz}$		4180		μF
Output Capacitance	C_{oss}			235		
Reverse Transfer Capacitance	C_{rss}			83		
Total Gate Charge ^c	Q_g	$V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$		64	100	nC
Gate-Source Charge ^c	Q_{gs}			23		
Gate-Drain Charge ^c	Q_{gd}			16		
Gate Resistance	R_g	$f = 1\text{ MHz}$		2.1	4.2	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 75\text{ V}, R_L = 0.88\text{ }\Omega$ $I_D = 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		15	25	ns
Rise Time ^c	t_r			10	15	
Turn-Off Delay Time ^c	$t_{d(off)}$			25	40	
Fall Time ^c	t_f			8	15	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}$ ^b						
Continuous Current	I_S				75	A
Pulsed Current	I_{SM}				180	
Forward Voltage ^a	V_{SD}	$I_F = 30\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		130	200	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			8	12	A
Reverse Recovery Charge	Q_{rr}			520	1200	nC

Notes:

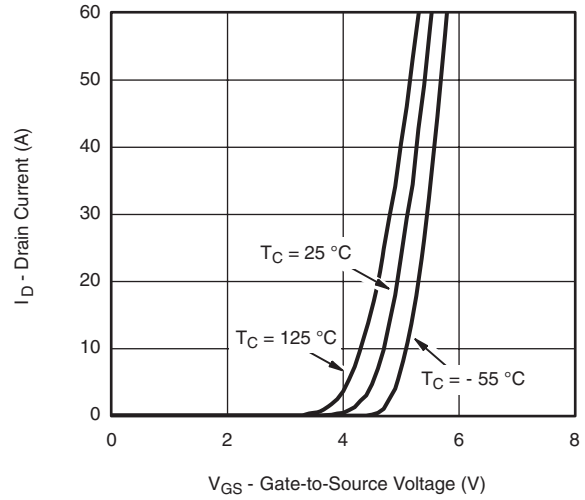
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

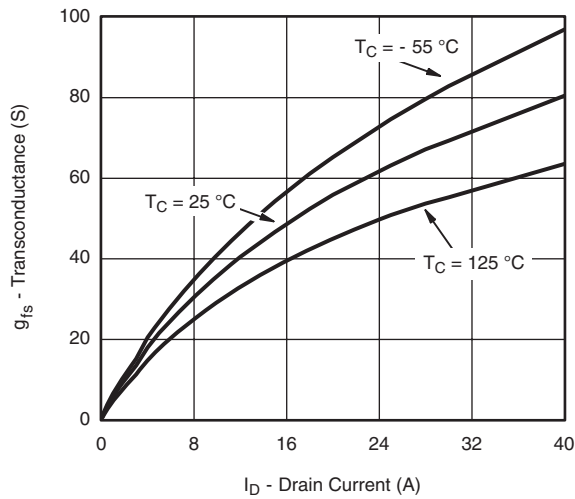
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



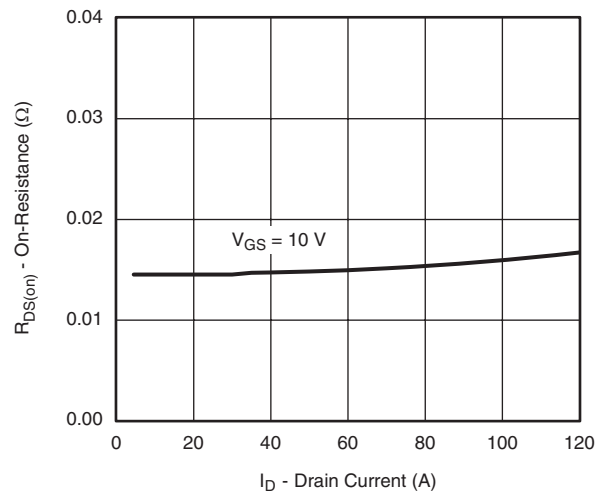
Output Characteristics



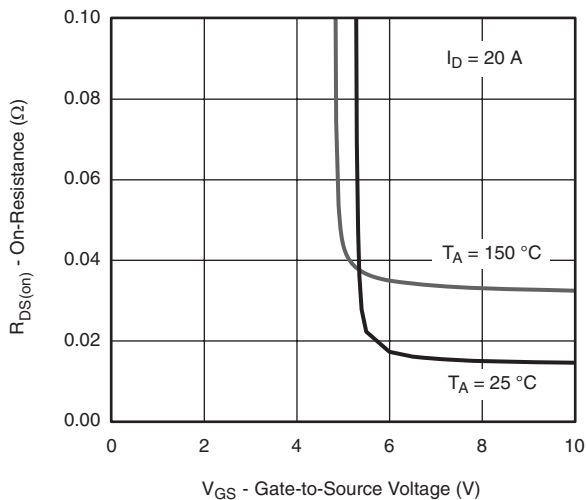
Transfer Characteristics



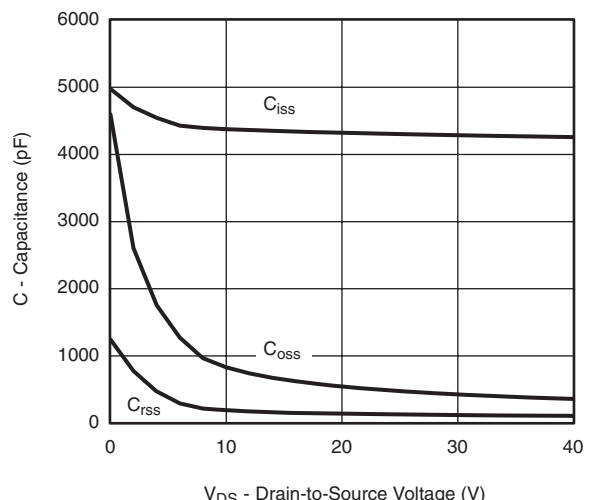
Transconductance



On-Resistance vs. Drain Current

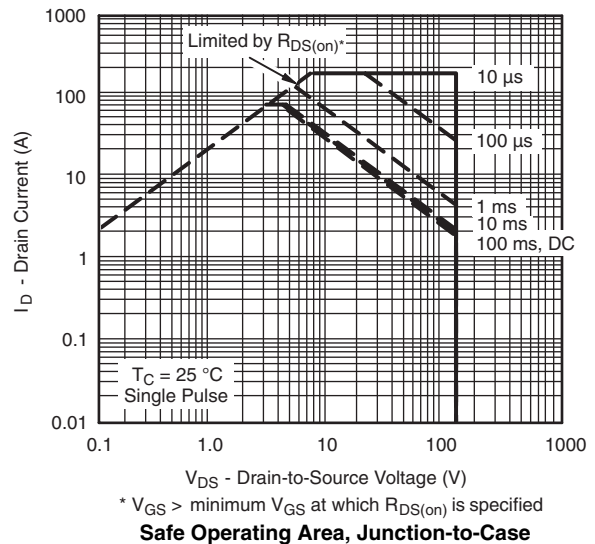
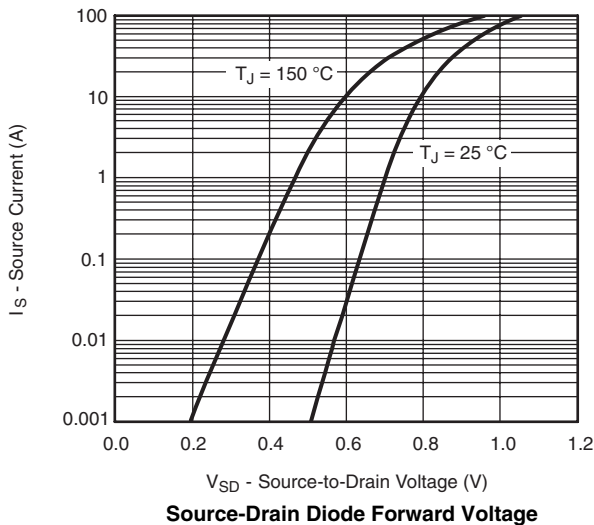
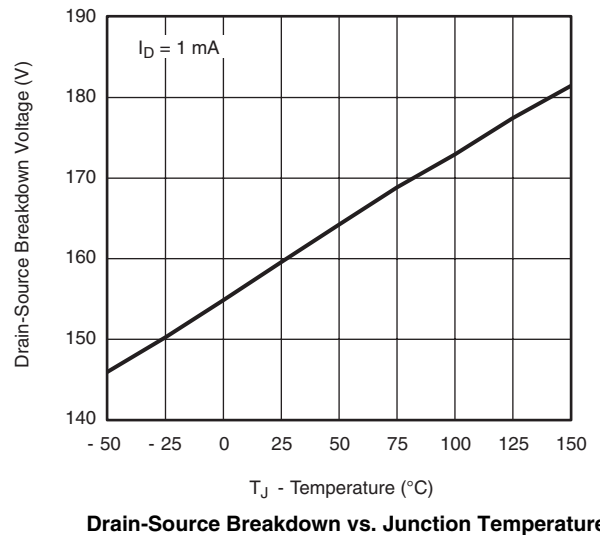
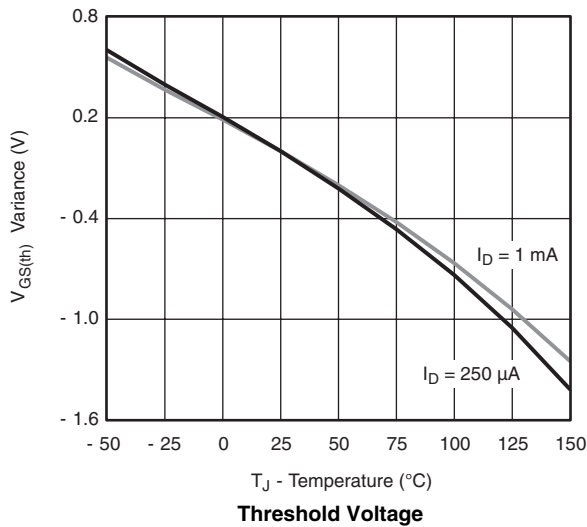
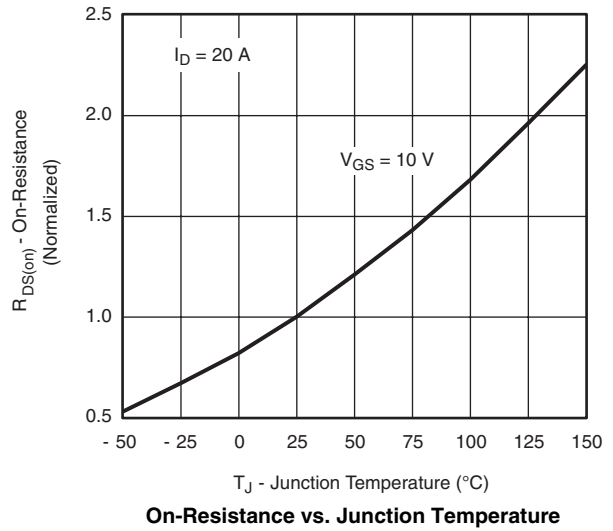
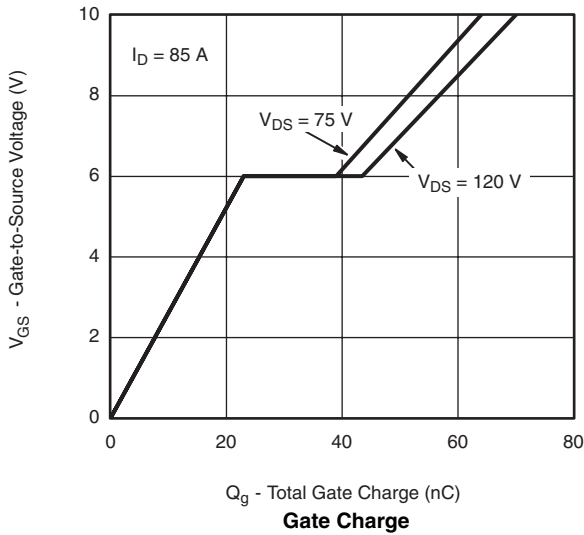


On-Resistance vs. Gate-to-Source Voltage

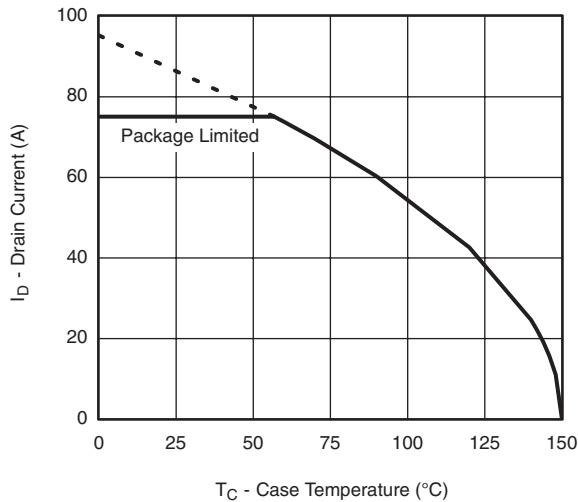


Capacitance

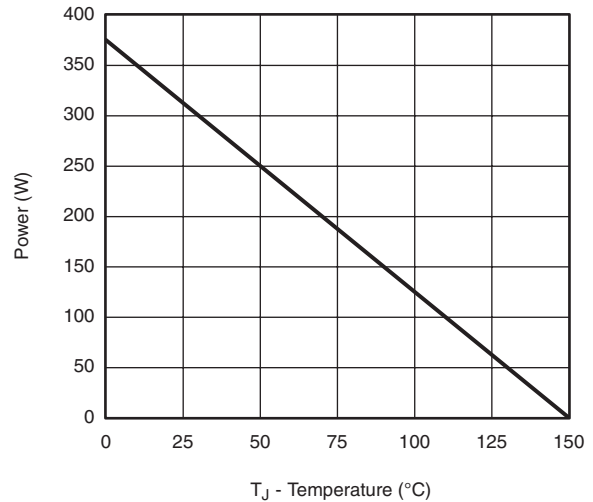
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



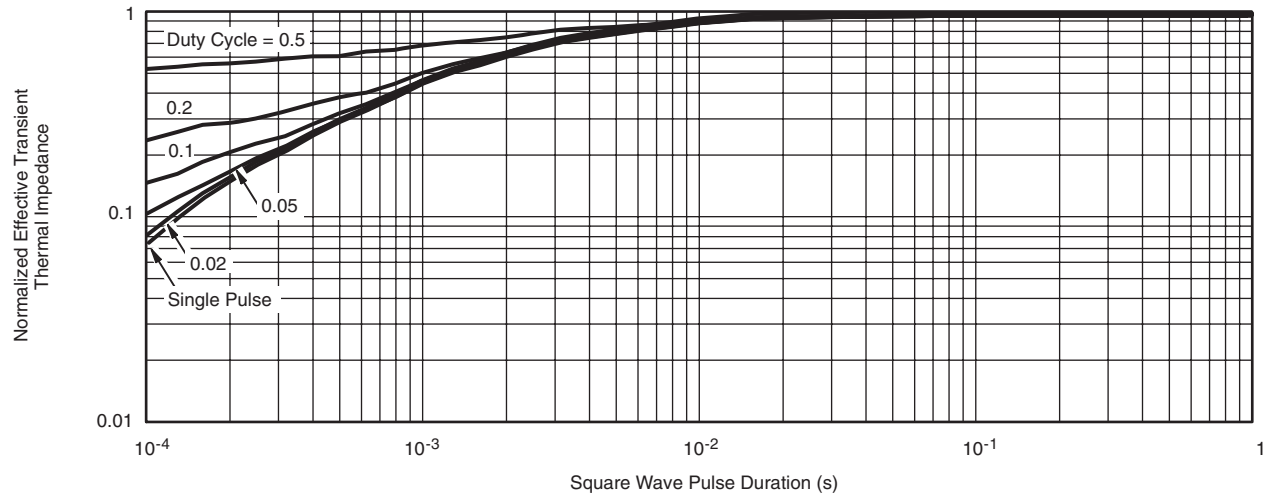
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*, Junction-to-Case



Power Derating*, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Case

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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